

SN74LV165A 8 位并联负载移位寄存器

1 特性

- 2 V 至 5.5 V V_{CC} 运行
- 5V 时 t_{pd} 最大值为 10.5 ns
- 所有端口上均支持以混合模式电压运行
- I_{off} 支持局部关断模式运行
- 闩锁性能超过 250mA，符合 JESD 17 规范

2 应用

- 增加微控制器上的输入数

3 说明

SN74LV165A 器件是 8 位并行负载移位寄存器，专为 2V 至 5.5V V_{CC} 操作而设计。

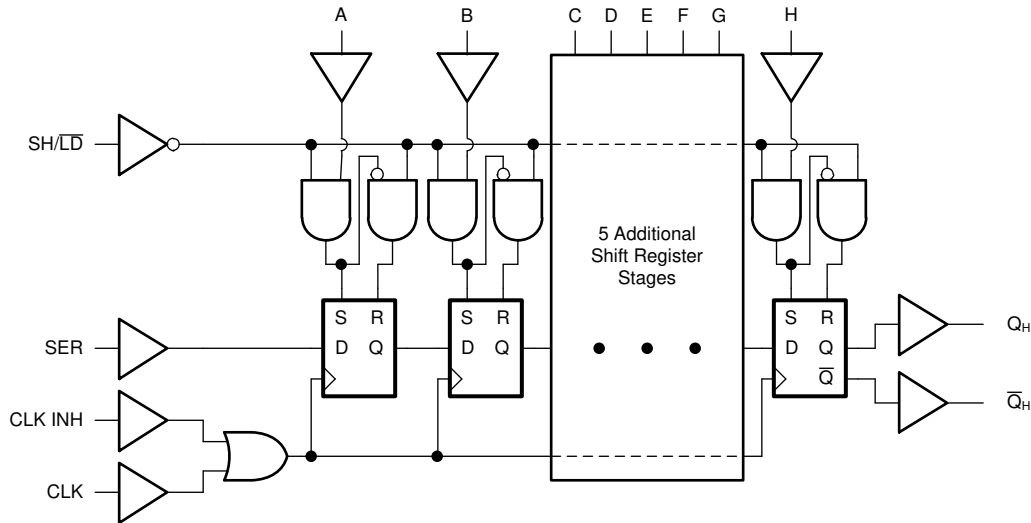
器件计时时，数据通过串行输出 Q_H 传输。当移位/负载 (SH/LD) 输入为低电平时，可支持八个单独的直接数据输入，从而实现在每个级的并行输入。LV165A 器件具有时钟抑制功能和补充串行输出 $\bar{Q}_H$ 。

该器件专用于使用 I_{off} 的局部断电应用。 I_{off} 电路会禁用输出，从而在器件断电时防止电流回流损坏器件。

器件信息(1)

器件型号	封装	封装尺寸 (标称值)
SN74LV165A	D (SOIC, 16)	9.90mm × 3.90mm
	DB (SSOP, 16)	6.20mm × 5.30mm
	NS (SO, 16)	10.20mm × 5.30mm
	PW (TSSOP, 16)	5.00mm × 4.40mm
	DGV (TVSOP, 16)	3.60mm × 4.40mm
	RGY (VQFN , 16)	4.00mm × 3.50mm
	BQB (WQFN , 16)	3.60mm × 2.60mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



逻辑图 (正逻辑)



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4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision P (June 2022) to Revision Q (December 2022)	Page
• 将数据表状态从“预告信息”更改为“生产数据”	1
Changes from Revision O (November 2016) to Revision P (June 2022)	Page
• 更新了整个文档中的表格、图和交叉参考的编号格式.....	1
• 向器件信息、引脚配置和热性能信息表中添加了 BQB (WQFN) 封装信息.....	1
• Updated specifications table formatting.....	6
Changes from Revision N (July 2013) to Revision O (November 2016)	Page
• 添加了应用部分、器件信息表、目录、引脚配置和功能部分、规格部分、ESD 等级表、热性能信息表、典型特性部分、详细说明部分、应用和实现部分、电源相关建议部分、布局部分、器件和文档支持部分以及机械、封装和可订购信息部分	1

5 Pin Configuration and Functions

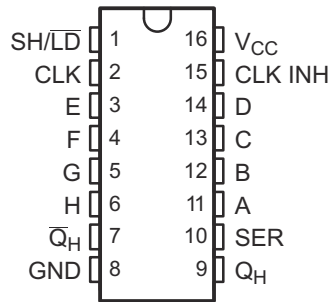


图 5-1. D, DB, DGV, N or PW Package,
16-Pin SOIC, SSOP, TVSOP, SOP or TSSOP
(Top View)

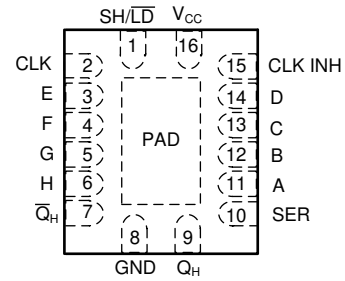


图 5-2. RGY or BQB Package,
16-Pin VQFN or WQFN
(Top View)

表 5-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
A	11	I	Serial input A
B	12	I	Serial input B
C	13	I	Serial input C
CLK	2	I	Storage clock
CLK INH	15	I	Storage clock
D	14	I	Serial input D
E	3	I	Serial input E
F	4	I	Serial input F
G	5	I	Serial input G
GND	8	G	Ground pin
H	6	I	Serial input H
$\bar{Q}_H$	7	O	Output H, inverted
Q_H	9	O	Output H
SH/ $\bar{LD}$	1	I	Load Input
SER	10	I	Serial input
V_{CC}	16	P	Power pin
PAD		—	Thermal Pad ⁽²⁾

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.

(2) RGY and BQB Package Only

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Supply voltage		- 0.5	7	V
Input voltage ⁽²⁾		- 0.5	7	V
Voltage range applied to any output in the high-impedance or power-off state ⁽²⁾		- 0.5	7	V
Output voltage ⁽²⁾ ⁽³⁾		- 0.5	$V_{CC} + 0.5$	V
Input clamp current	$V_I < 0$		- 20	mA
Output clamp current	$V_O < 0$		- 50	mA
Continuous output current	$V_O = 0$ to V_{CC}		±25	mA
Continuous current through V_{CC} or GND			±50	mA
T_{jmax}	Maximum virtual junction temperature		150	°C
T_{stg}	Storage temperature	- 65	150	°C

- (1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) This value is limited to 5.5 V maximum.

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge		
	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
	Machine Model (MM), per JEDEC specification	±200	
	Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		2	5.5	V
V _{IH}	High-level input voltage	V _{CC} = 2 V	1.5		V
		V _{CC} = 2.3 V to 2.7 V	V _{CC} × 0.7		
		V _{CC} = 3 V to 3.6 V	V _{CC} × 0.7		
		V _{CC} = 4.5 V to 5.5 V	V _{CC} × 0.7		
V _{IL}	Low-level input voltage	V _{CC} = 2 V		0.5	V
		V _{CC} = 2.3 V to 2.7 V		V _{CC} × 0.3	
		V _{CC} = 3 V to 3.6 V		V _{CC} × 0.3	
		V _{CC} = 4.5 V to 5.5 V		V _{CC} × 0.3	
V _I	Input voltage		0	5.5	V
V _O	Output voltage		0	V _{CC}	V
I _{OH}	High-level output current	V _{CC} = 2 V		– 50	μA
		V _{CC} = 2.3 V to 2.7 V		– 2	mA
		V _{CC} = 3 V to 3.6 V		– 6	
		V _{CC} = 4.5 V to 5.5 V		– 12	
I _{OL}	Low-level output current	V _{CC} = 2 V		50	μA
		V _{CC} = 2.3 V to 2.7 V		2	mA
		V _{CC} = 3 V to 3.6 V		6	
		V _{CC} = 4.5 V to 5.5 V		12	
Δ t / Δ v	Input transition rise or fall rate	V _{CC} = 2.3 V to 2.7 V		200	ns/V
		V _{CC} = 3 V to 3.6 V		100	
		V _{CC} = 4.5 V to 5.5 V		20	
T _A	Operating free-air temperature		– 40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See [Implications of Slow or Floating CMOS Inputs](#)

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74LV165A							UNIT
		D (SOIC)	DB (SSOP)	NS (SO)	PW (TSSOP)	DGV (TVSOP)	RGY (VQFN)	BQB (WQFN)	
		16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	86.2	102.8	89.4	113.3	125.9	48.8	85.9	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	46.1	53.3	47.9	48.3	51	46.7	82.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	43.8	53.5	49.8	58.4	57.7	24.9	55.6	°C/W
ψ _{JT}	Junction-to-top characterization parameter	13.2	16.6	16.6	6.4	5.7	2	9.4	°C/W
ψ _{JB}	Junction-to-board characterization parameter	43.5	52.9	49.5	57.8	57.2	24.9	55.6	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	N/A	11.7	33.3	°C/W

(1) For more information about traditional and new thermal metrics, see [Semiconductor and IC Package Thermal Metrics](#)

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted).

PARAMETER		TEST CONDITIONS	V _{CC}	- 40°C to 85°C			- 40°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
V _{OH}	High-level output voltage	I _{OH} = - 50 mA	2 V to 5.5 V	V _{CC} - 0.1			V _{CC} - 0.1			V
		I _{OH} = - 2 mA	2.3 V	2			2			
		I _{OH} = - 6 mA	3 V	2.48			2.48			
		I _{OH} = - 12 mA	4.5 V	3.8			3.8			
V _{OL}	Low-level output voltage	I _{OL} = 50 mA	2 V to 5.5 V	0.1			0.1			V
		I _{OL} = 2 mA	2.3 V	0.4			0.4			
		I _{OL} = 6 mA	3 V	0.44			0.44			
		I _{OL} = 12 mA	4.5 V	0.55			0.55			
I _I	Input leakage current	V _I = 5.5 V or GND	0 V to 5.5 V	±1			±1			μA
I _{CC}	Static supply current	V _I = V _{CC} or GND, I _O = 0	5.5 V	20			20			μA
I _{off}	Partial power down current	V _I or V _O = 0 to 5.5 V	0	5			5			μA
C _i	Input capacitance	V _I = V _{CC} or GND	3.3 V	1.7			1.7			pF

6.6 Timing Requirements, V_{CC} = 2.5 V ± 0.2 V

over recommended operating free-air temperature range (unless otherwise noted) (see 图 7-1)

PARAMETER	TEST CONDITION	25°C		- 40°C to 85°C		- 40°C to 125°C		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t _w Pulse duration	CLK high or low	8.5		9		9		ns
	SH/ $\overline{\text{LD}}$ low	11		13		13		
t _{su} Setup time	SH/ $\overline{\text{LD}}$ high before CLK ↑	7		8.5		8.5		ns
	SER before CLK ↑	8.5		9.5		9.5		
	CLK INH before CLK ↑	7		7		7		
	Data before SH/ $\overline{\text{LD}}$ ↑	11.5		12		12		
t _h Hold time	SER data after CLK ↑	-1		0		0		ns
	Parallel data after SH/ $\overline{\text{LD}}$ ↑	0		0		0		
	SH/ $\overline{\text{LD}}$ high after CLK ↑	0		0		0		

6.7 Timing Requirements, V_{CC} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range (unless otherwise noted) (see 图 7-1)

PARAMETER	TEST CONDITION	25°C		- 40°C to 85°C		- 40°C to 125°C		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t _w Pulse duration	CLK high or low	6		7		7		ns
	SH/ $\overline{\text{LD}}$ low	7.5		9		9		
t _{su} Setup time	SH/ $\overline{\text{LD}}$ high before CLK ↑	5		6		6		ns
	SER before CLK ↑	5		6		6		
	CLK INH before CLK ↑	5		5		5		
	Data before SH/ $\overline{\text{LD}}$ ↑	7.5		8.5		8.5		
t _h Hold time	SER data after CLK ↑	0		0		0		ns
	Parallel data after SH/ $\overline{\text{LD}}$ ↑	0.5		0.5		0.5		
	SH/ $\overline{\text{LD}}$ high after CLK ↑	0		0		0		

6.8 Timing Requirements, $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted) (see 图 7-1)

PARAMETER	TEST CONDITION	25°C		– 40°C to 85°C		– 40°C to 125°C		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t_w Pulse duration	CLK high or low	4		4		4		ns
	SH/ $\overline{\text{LD}}$ low	5		6		6		
t_{su} Setup time	SH/ $\overline{\text{LD}}$ high before CLK $\uparrow$	4		4		4		ns
	SER before CLK $\uparrow$	4		4		4		
	CLK INH before CLK $\uparrow$	3.5		3.5		3.5		
	Data before SH/ $\overline{\text{LD}}$ $\uparrow$	5		5		5		
t_h Hold time	SER data after CLK $\uparrow$	0.5		0.5		0.5		ns
	Parallel data after SH/ $\overline{\text{LD}}$ $\uparrow$	1		1		1		
	SH/ $\overline{\text{LD}}$ high after CLK $\uparrow$	0.5		0.5		0.5		

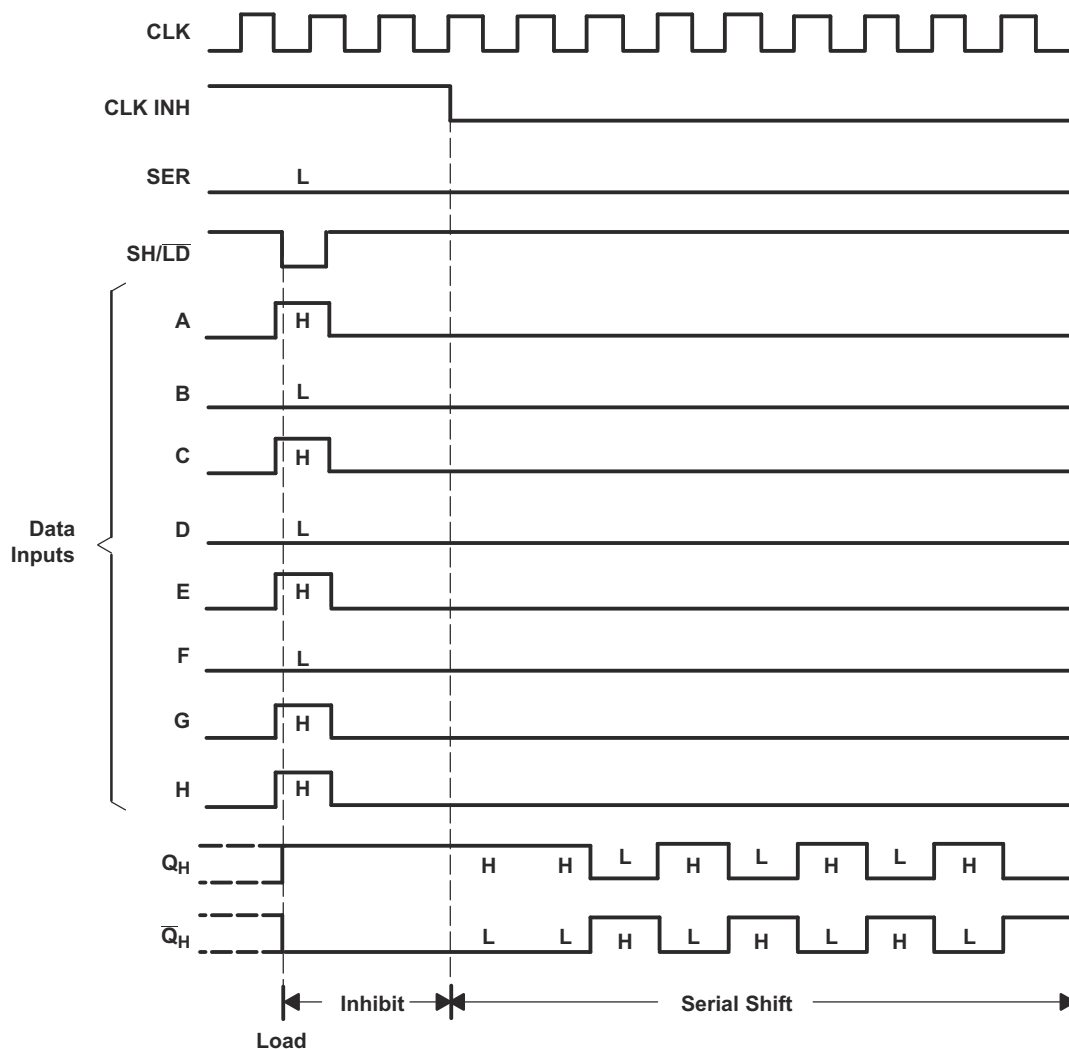


图 6-1. Typical Shift, Load, and Inhibit Sequences

6.9 Switching Characteristics, $V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$

over operating free-air temperature range (unless otherwise noted), (see 图 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAP	25°C			– 40°C to 85°C			– 40°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
$f_{\max}$			$C_L = 15\text{ pF}$	50	80		45			45			MHz
			$C_L = 50\text{ pF}$	40	65		35			35			
t_{pd}	CLK	Q_H or $\bar{Q}$	$C_L = 15\text{ pF}$		12.2	19.8		1		22		1	ns
	SH/ $\bar{LD}$				13.1	21.5		1		23.5		1	
	H				12.9	21.7		1		24		1	
t_{pd}	CLK	Q_H or $\bar{Q}$	$C_L = 50\text{ pF}$		15.3	23.3		1		26		1	ns
	SH/ $\bar{LD}$				16.1	25.1		1		28		1	
	H				15.9	25.3		1		28		1	

6.10 Switching Characteristics, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$

over operating free-air temperature range (unless otherwise noted), (see 图 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAP	25°C			– 40°C to 85°C			– 40°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
$f_{\max}$			$C_L = 15\text{ pF}$	65	115		55			55			MHz
			$C_L = 50\text{ pF}$	60	90		50			50			
t_{pd}	CLK	Q_H or $\bar{Q}$	$C_L = 15\text{ pF}$		8.6	15.4		1		18		1	ns
	SH/ $\bar{LD}$				9.1	15.8		1		18.5		1	
	H				8.9	14.1		1		16.5		1	
t_{pd}	CLK	Q_H or $\bar{Q}$	$C_L = 50\text{ pF}$		10.9	14.9		1		16.9		1	ns
	SH/ $\bar{LD}$				11.3	19.3		1		22		1	
	H				11.1	17.6		1		20		1	

6.11 Switching Characteristics, $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

over recommended operating free-air temperature range (see 图 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAP	25°C			– 40°C to 85°C			– 40°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
$f_{\max}$			$C_L = 15\text{ pF}$	110	165		90			90			MHz
			$C_L = 50\text{ pF}$	95	125		85			85			
t_{pd}	CLK	Q_H or $\bar{Q}$	$C_L = 15\text{ pF}$		6	9.9		1		11.5		1	ns
	SH/ $\bar{LD}$				6	9.9		1		11.5		1	
	H				6	9.9		1		10.5		1	
t_{pd}	CLK	Q_H or $\bar{Q}$	$C_L = 50\text{ pF}$		7.7	11.9		1		13.5		1	ns
	SH/ $\bar{LD}$				7.7	11.9		1		13.5		1	
	H				7.6	11		1		12.5		1	

6.12 Operating Characteristics

$T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	$C_L = 50\text{ pF}$	$f = 10\text{ MHz}$	3.3 V	36.1	pF
				5 V	37.5	

6.13 Typical Characteristics

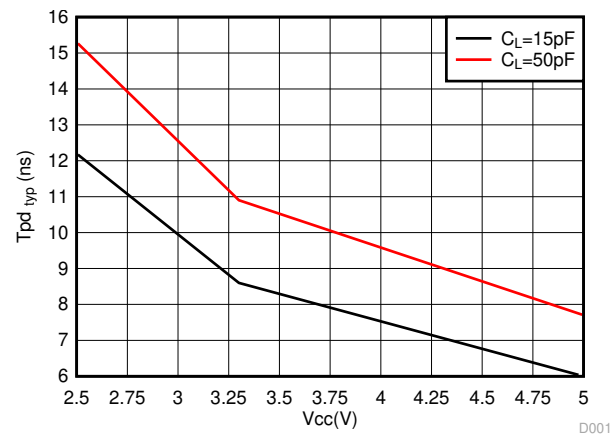
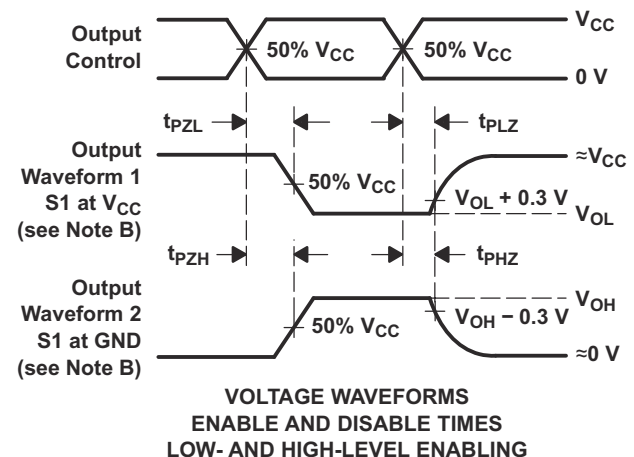
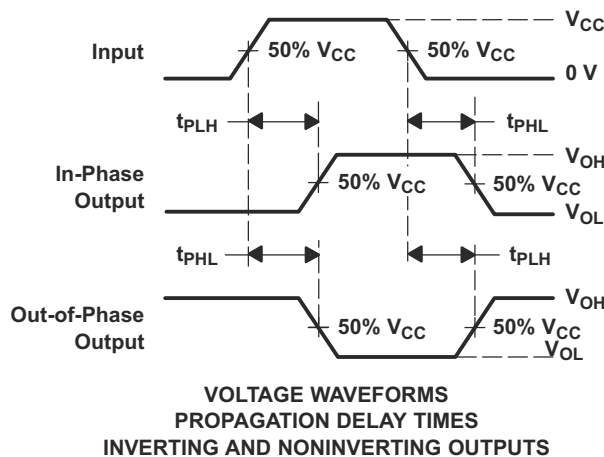
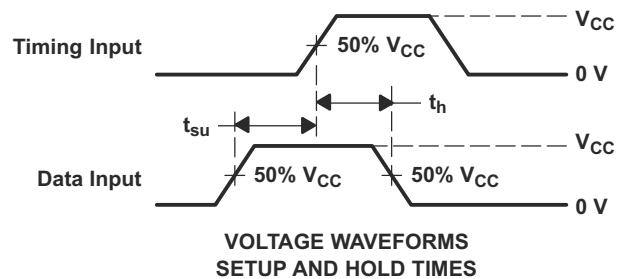
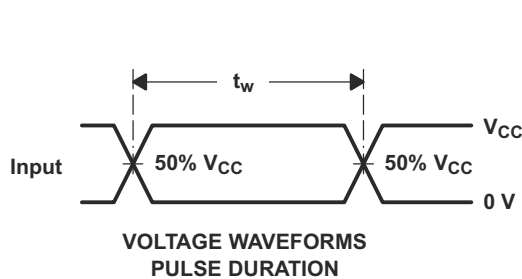
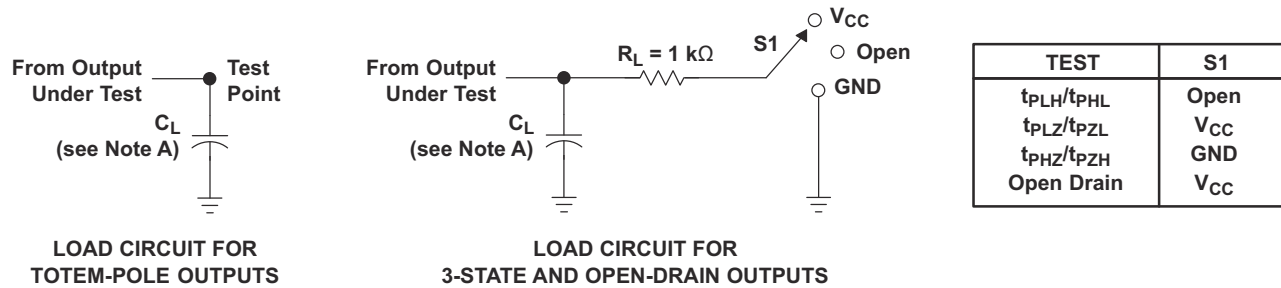


图 6-2. T_{PD} Typical (25°C) vs V_{CC}

7 Parameter Measurement Information



- C_L includes probe and jig capacitance.
- Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- All input pulses are supplied by generators having the following characteristics: $PRR \leq 1 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 3 \text{ ns}$, $t_f \leq 3 \text{ ns}$.
- The outputs are measured one at a time, with one input transition per measurement.
- t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- t_{PZL} and t_{PZH} are the same as t_{en} .
- t_{PHL} and t_{PLH} are the same as t_{pd} .
- All parameters and waveforms are not applicable to all devices.

图 7-1. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

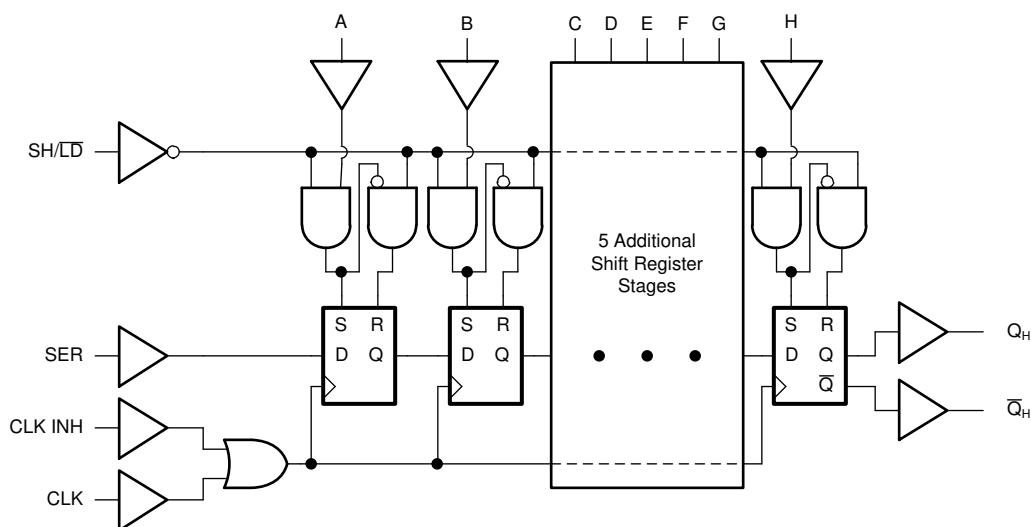
The SN74LV165A device is a parallel-load, 8-bit shift registers designed for 2 V to 5.5 V V_{CC} operation.

When the device is clocked, data is shifted toward the serial output Q_H . Parallel-in access to each stage is provided by eight individual direct data inputs that are enabled by a low level at the shift/load ($SH/\overline{LD}$) input. The SN74LV165A devices feature a clock-inhibit function and a complemented serial output, $\overline{Q}_H$.

Clocking is accomplished by a low-to-high transition of the clock (CLK) input while $SH/\overline{LD}$ is held high and clock inhibit (CLK INH) is held low. The functions of CLK and CLK INH are interchangeable. Since a low CLK and a low-to-high transition of CLK INH accomplishes clocking, CLK INH must be changed to the high level only while CLK is high. Parallel loading is inhibited when $SH/\overline{LD}$ is held high. The parallel inputs to the register are enabled while $SH/\overline{LD}$ is held low, independently of the levels of CLK, CLK INH, or SER.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

8.3.2 Latching Logic

This device includes latching logic circuitry. Latching circuits commonly include D-type latches and D-type flip-flops, but include all logic circuits that act as volatile memory.

When the device is powered on, the state of each latch is unknown. There is no default state for each latch at start-up.

The output state of each latching logic circuit only remains stable as long as power is applied to the device within the supply voltage range specified in the *Recommended Operating Conditions* table.

8.3.3 Partial Power Down (I_{off})

This device includes circuitry to disable all outputs when the supply pin is held at 0 V. When disabled, the outputs will neither source nor sink current, regardless of the input voltages applied. The amount of leakage current at each output is defined by the I_{off} specification in the *Electrical Characteristics* table.

8.3.4 Clamp Diode Structure

图 8-1 shows the inputs and outputs to this device have negative clamping diodes only.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

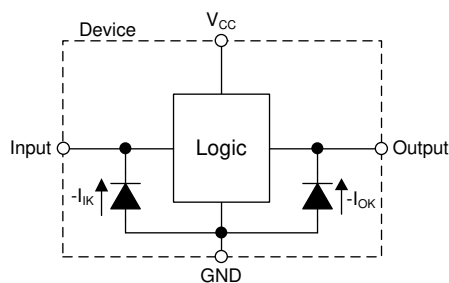


图 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

The [Operating Mode Table](#) and the [Output Function Table](#) list the functional modes of the SN74LV165A.

表 8-1. Operating Mode Table

INPUTS ⁽¹⁾			FUNCTION
SH/LD	CLK	CLK INH	
L	X	X	Parallel load
H	H	X	No change
H	X	H	No change
H	L	↑	Shift ⁽²⁾
H	↑	L	Shift ⁽²⁾

(1) H = High Voltage Level, L = Low Voltage Level, X = Do Not Care, ↑ = Low to High transition

(2) Shift : Content of each internal register shifts towards serial output Q_H. Data at SER is shifted into the first register.

表 8-2. Output Function Table

INTERNAL REGISTERS ^{(1) (2)}		OUTPUTS ⁽²⁾	
A — G	H	Q	Q̄
X	L	L	H
X	H	H	L

(1) Internal registers refer to the shift registers inside the device. These values are set by either loading data from the parallel inputs, or by clocking data in from the serial input.

(2) H = High Voltage Level, L = Low Voltage Level, X = Do Not Care

9 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

9.1 Application Information

The SN74LV165A is a low drive CMOS device that can be used for a multitude of bus interface type applications where output ringing is a concern. The low-drive and slow-edge rates minimize overshoot and undershoot on the outputs.

9.2 Typical Application

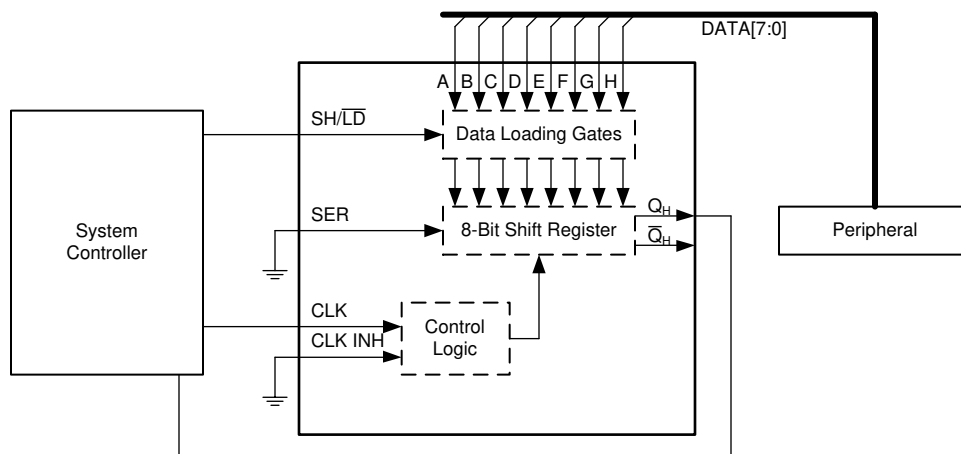


图 9-1. Input Expansion with Shift Registers

9.2.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LV165A plus the maximum static supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LV165A plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74LV165A can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74LV165A can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and Cpd Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LV165A (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k Ω resistor value is often used due to these factors.

The SN74LV165A has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

9.2.4 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; it will, however, ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74LV165A to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in $M\Omega$; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

9.2.5 Application Curve

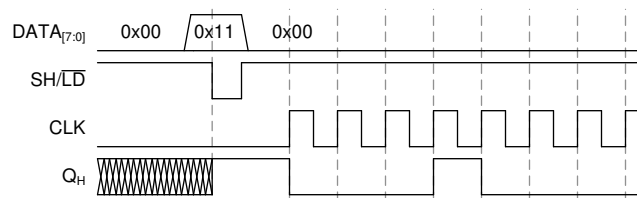


图 9-2. Application Timing Diagram

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the [§ 6.1](#) section. Each V_{CC} terminal must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, TI recommends a 0.1- μ F capacitor and if there are multiple V_{CC} terminals then TI recommends a 0.01- μ F or 0.022- μ F capacitor for each power terminal. Multiple bypass capacitors can be paralleled to reject different frequencies of noise. Frequencies of 0.1 μ F and 1 μ F are commonly used in parallel. The bypass capacitor must be installed as close as possible to the power terminal for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

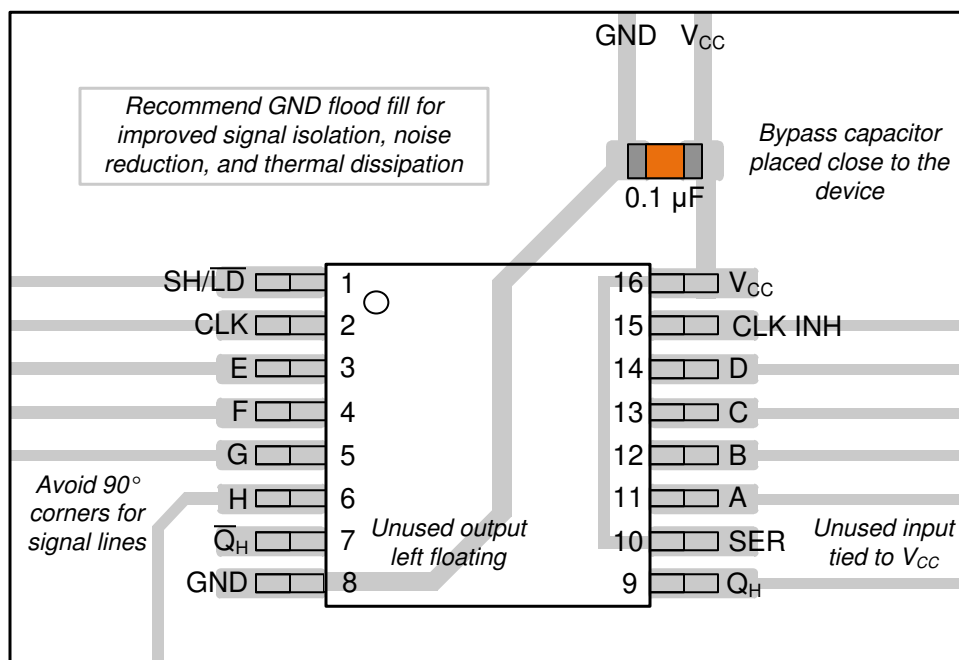


图 11-1. Example Layout for the SN74LV165A in the PW Package

12 Device and Documentation Support

12.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [Power-Up Behavior of Clocked Devices](#)
- Texas Instruments, [Introduction to Logic](#)

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates—including silicon errata—go to the product folder for your device on [ti.com](#). In the upper right-hand corner, click the *Alert me* button. This registers you to receive a weekly digest of product information that has changed (if any). For change details, check the revision history of any revised document.

12.3 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

12.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

所有商标均为其各自所有者的财产。

12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 术语表

TI 术语表 本术语表列出并解释了术语、首字母缩略词和定义。

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
PSN74LV165ABQBR	ACTIVE	WQFN	BQB	16	3000	TBD	Call TI	Call TI	-40 to 125		Samples
SN74LV165ABQBR	ACTIVE	WQFN	BQB	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165AD	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165ADBR	ACTIVE	SSOP	DB	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165ADE4	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165ADG4	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165ADGVR	ACTIVE	TVSOP	DGV	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165ADR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165ADRE4	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165ADRG3	ACTIVE	SOIC	D	16	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165ADRG4	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165ANSR	ACTIVE	SO	NS	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	74LV165A	Samples
SN74LV165APW	ACTIVE	TSSOP	PW	16	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165APWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165APWRE4	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165APWRG3	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165APWRG4	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165APWT	ACTIVE	TSSOP	PW	16	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A	Samples
SN74LV165ARGYR	ACTIVE	VQFN	RGY	16	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LV165A	Samples
SN74LV165ARGYRG4	ACTIVE	VQFN	RGY	16	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LV165A	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of ≤ 1000 ppm threshold. Antimony trioxide based flame retardants must also meet the ≤ 1000 ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LV165A :

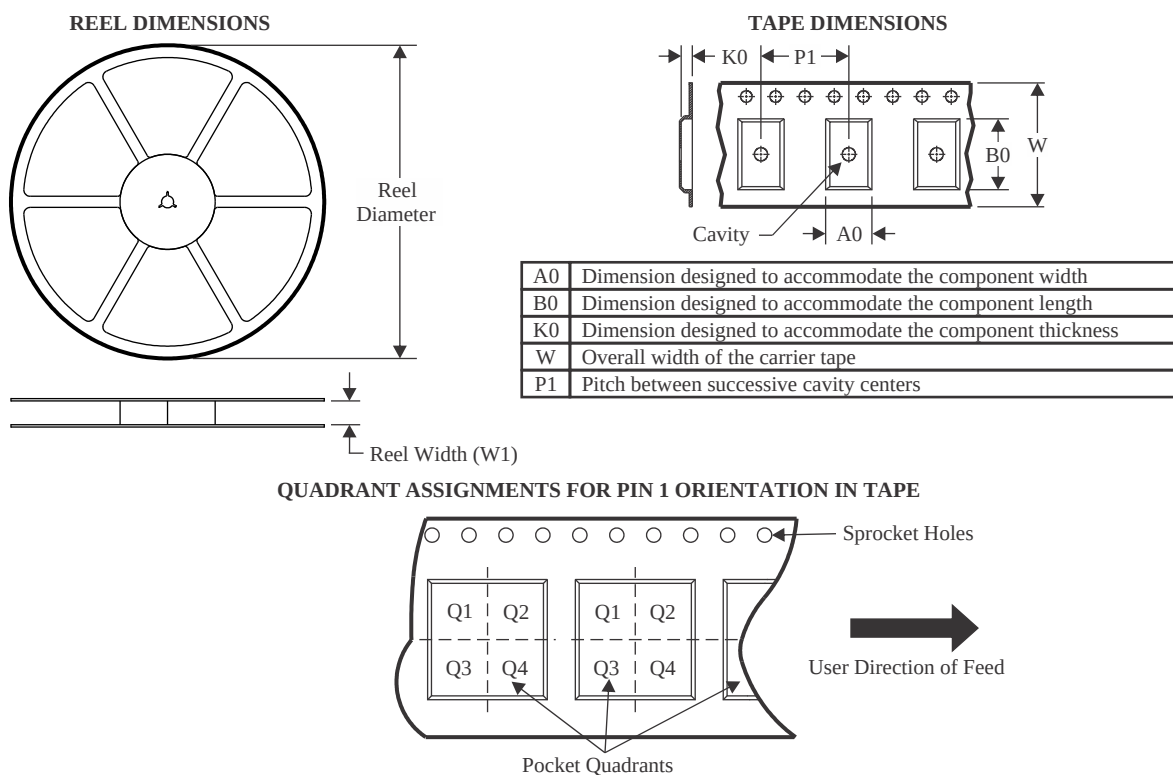
● Automotive : [SN74LV165A-Q1](#)

● Enhanced Product : [SN74LV165A-EP](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

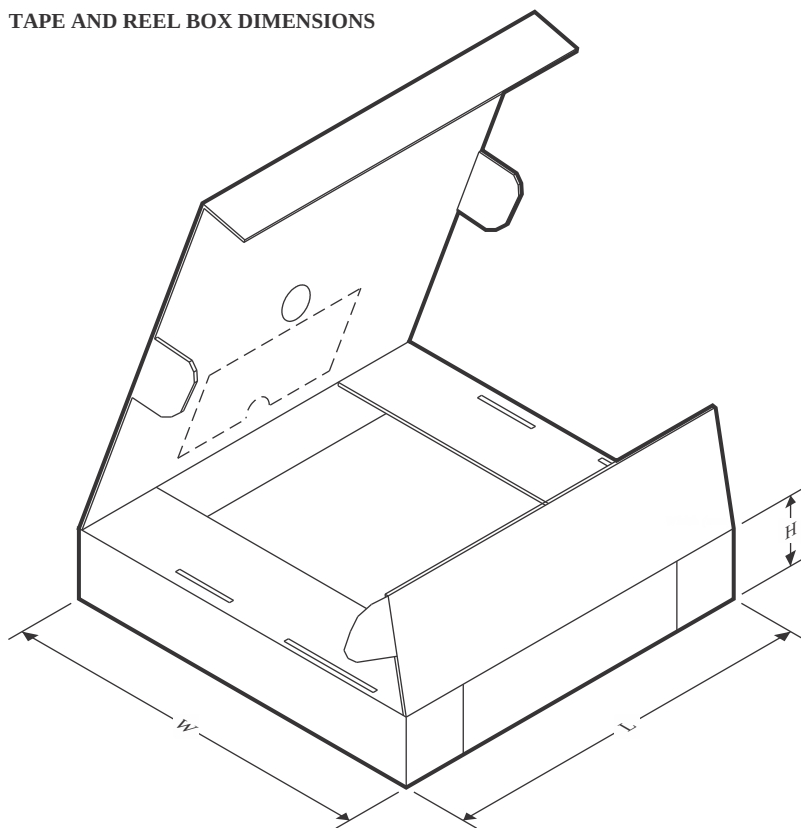
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LV165ABQBR	WQFN	BQB	16	3000	180.0	12.4	2.8	3.8	1.2	4.0	12.0	Q1
SN74LV165ADBR	SSOP	DB	16	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN74LV165ADGVR	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74LV165ADR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74LV165ADR	SOIC	D	16	2500	330.0	16.8	6.5	10.3	2.1	8.0	16.0	Q1
SN74LV165ADRG3	SOIC	D	16	2500	330.0	16.8	6.5	10.3	2.1	8.0	16.0	Q1
SN74LV165ADRG4	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74LV165ANSR	SO	NS	16	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN74LV165APWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV165APWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV165APWRG3	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV165APWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV165APWT	TSSOP	PW	16	250	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV165ARGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1
SN74LV165ARGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1

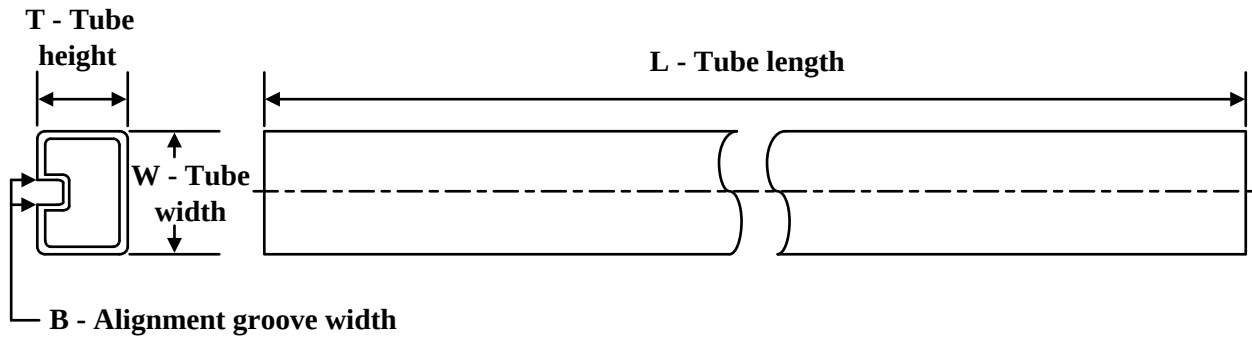
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LV165ABQBR	WQFN	BQB	16	3000	210.0	185.0	35.0
SN74LV165ADBR	SSOP	DB	16	2000	356.0	356.0	35.0
SN74LV165ADGVR	TVSOP	DGV	16	2000	356.0	356.0	35.0
SN74LV165ADR	SOIC	D	16	2500	340.5	336.1	32.0
SN74LV165ADR	SOIC	D	16	2500	364.0	364.0	27.0
SN74LV165ADRG3	SOIC	D	16	2500	364.0	364.0	27.0
SN74LV165ADRG4	SOIC	D	16	2500	340.5	336.1	32.0
SN74LV165ANSR	SO	NS	16	2000	356.0	356.0	35.0
SN74LV165APWR	TSSOP	PW	16	2000	356.0	356.0	35.0
SN74LV165APWR	TSSOP	PW	16	2000	364.0	364.0	27.0
SN74LV165APWRG3	TSSOP	PW	16	2000	364.0	364.0	27.0
SN74LV165APWRG4	TSSOP	PW	16	2000	356.0	356.0	35.0
SN74LV165APWT	TSSOP	PW	16	250	356.0	356.0	35.0
SN74LV165ARGYR	VQFN	RGY	16	3000	356.0	356.0	35.0
SN74LV165ARGYR	VQFN	RGY	16	3000	355.0	350.0	50.0

TUBE

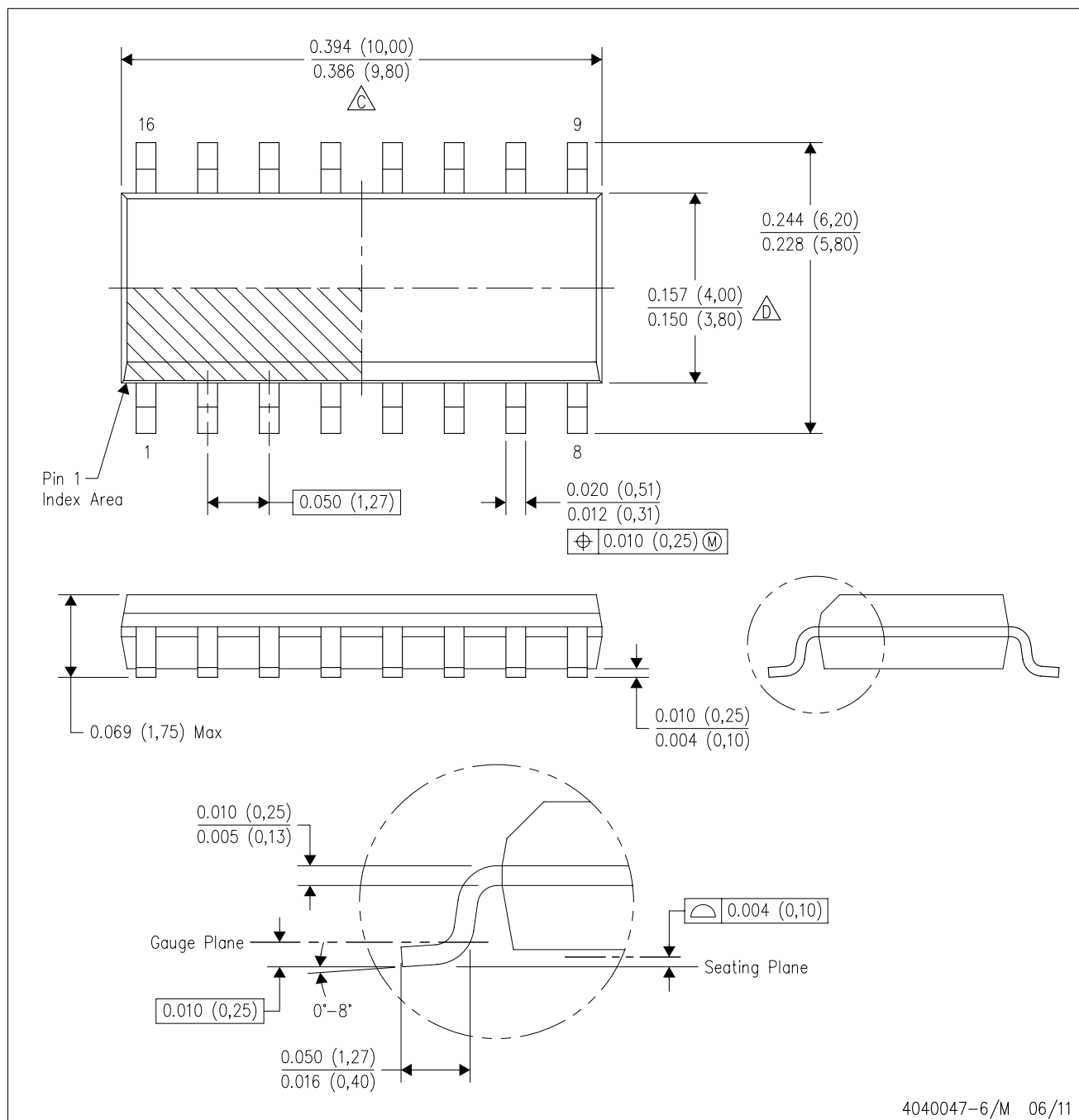


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN74LV165AD	D	SOIC	16	40	507	8	3940	4.32
SN74LV165ADE4	D	SOIC	16	40	507	8	3940	4.32
SN74LV165ADG4	D	SOIC	16	40	507	8	3940	4.32
SN74LV165APW	PW	TSSOP	16	90	530	10.2	3600	3.5

D (R-PDSO-G16)

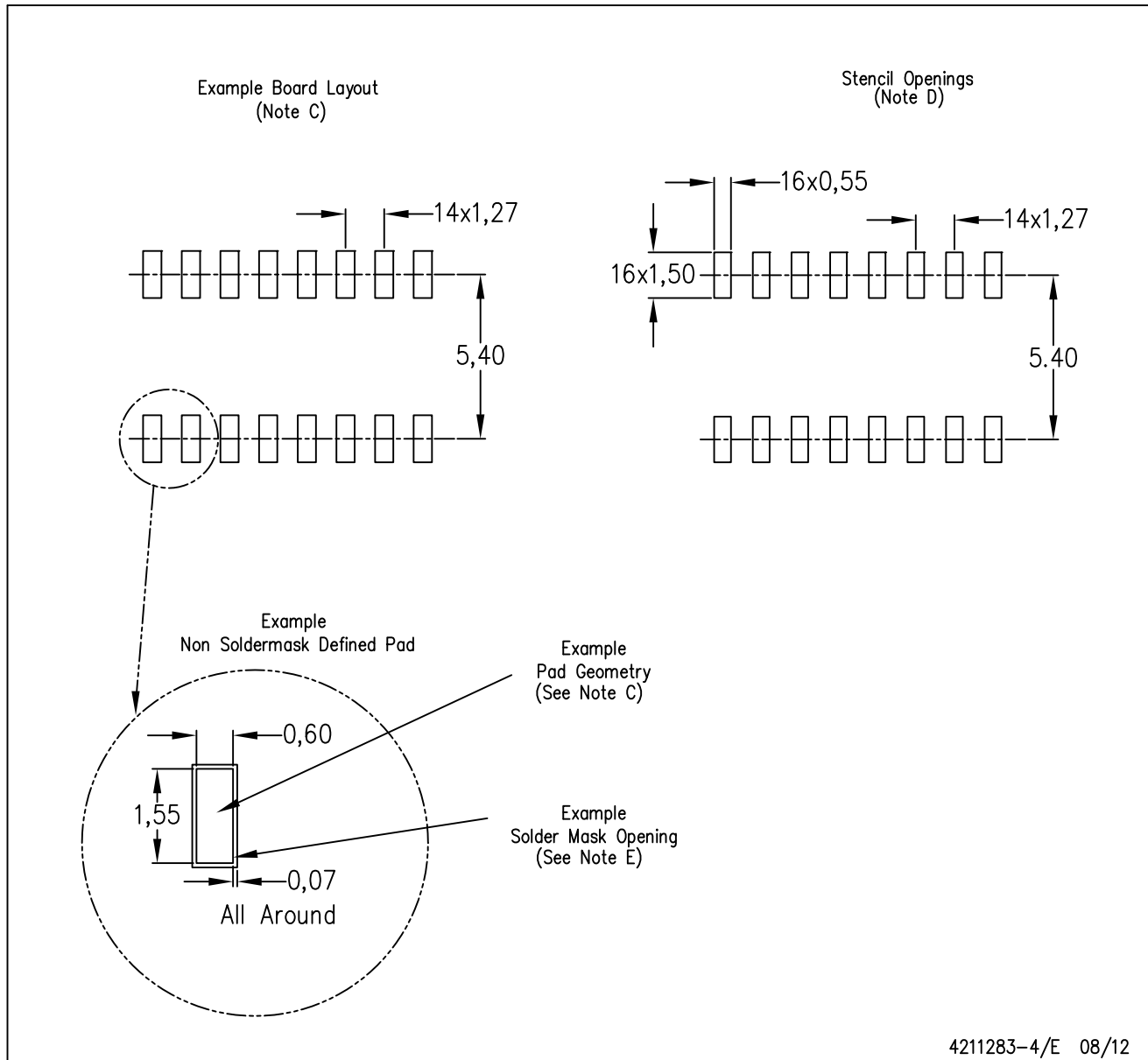
PLASTIC SMALL OUTLINE



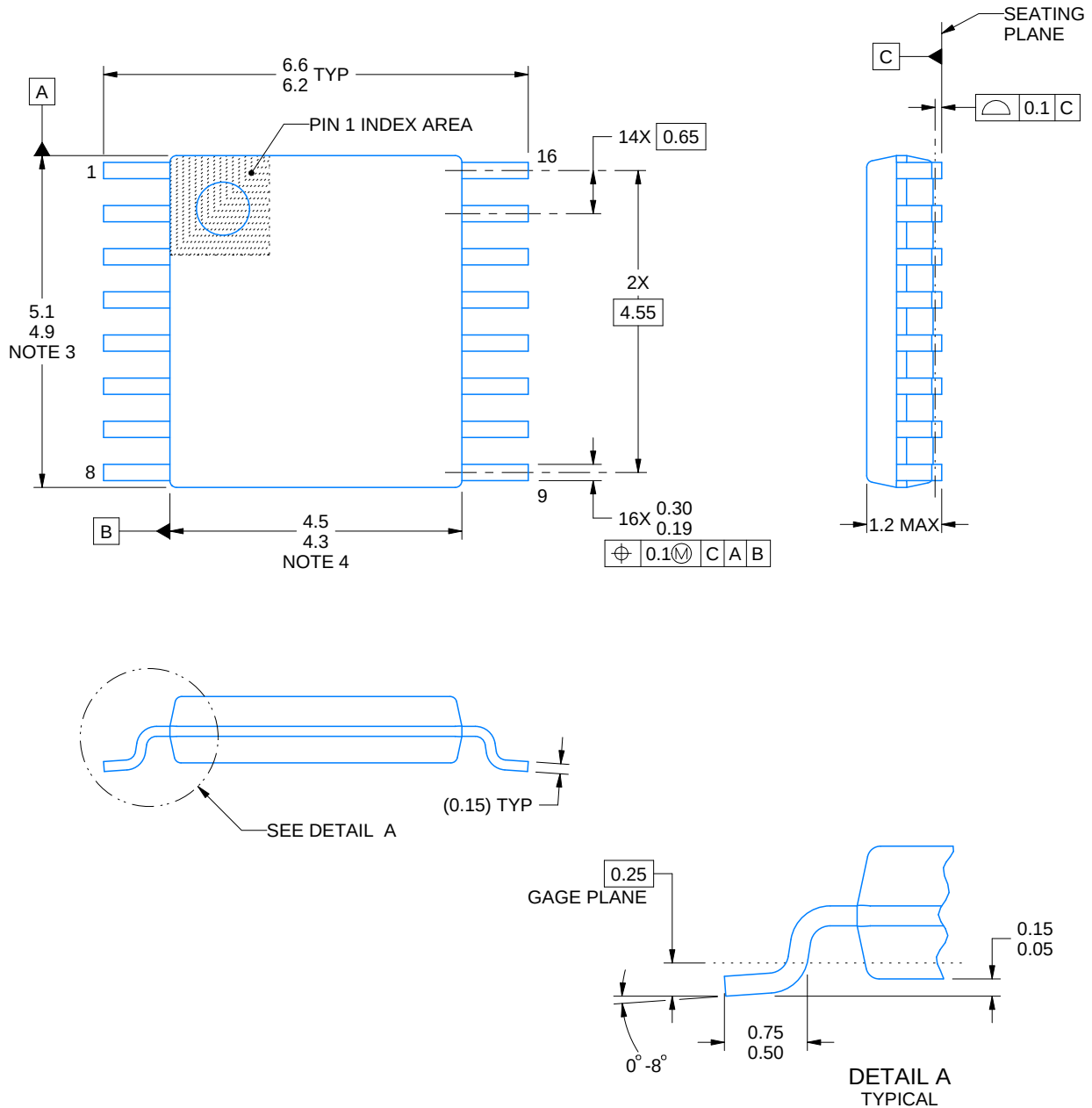
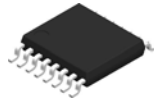
- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - $\triangle C$ Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 - $\triangle D$ Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 - E. Reference JEDEC MS-012 variation AC.

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



4220204/A 02/2017

NOTES:

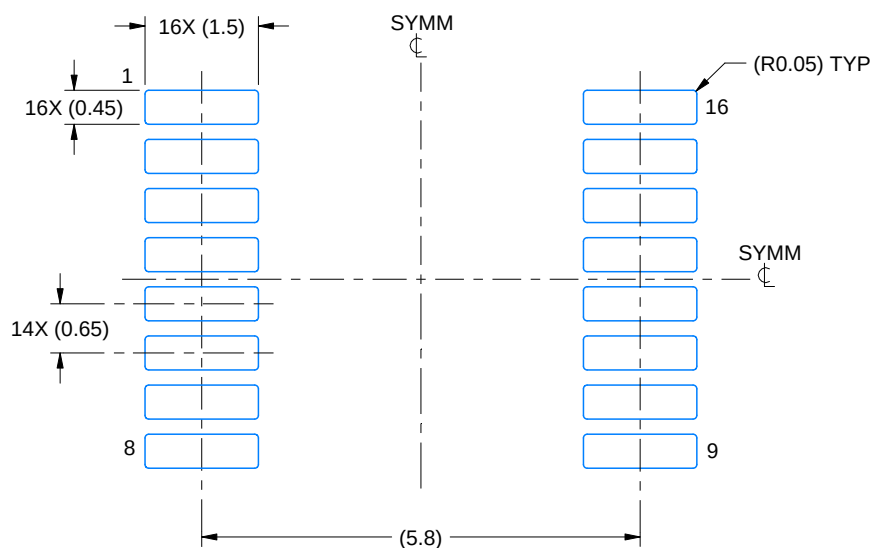
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

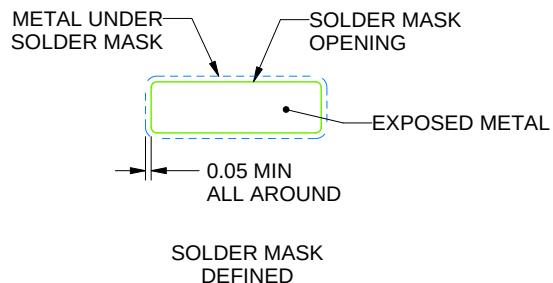
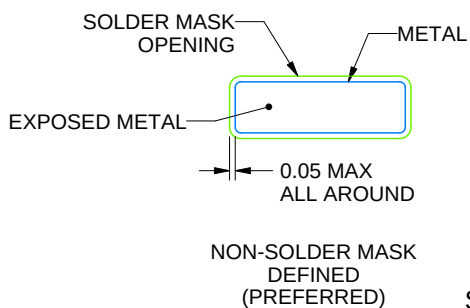
PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

4220204/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

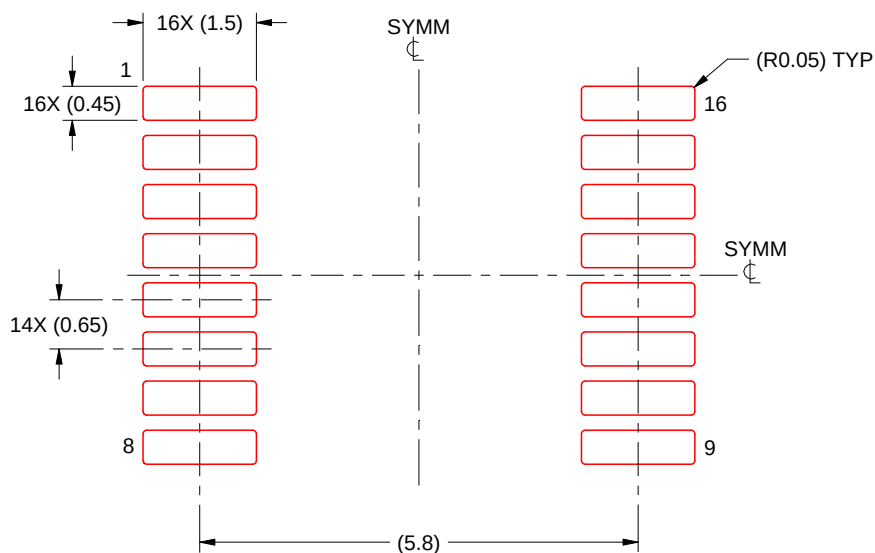
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

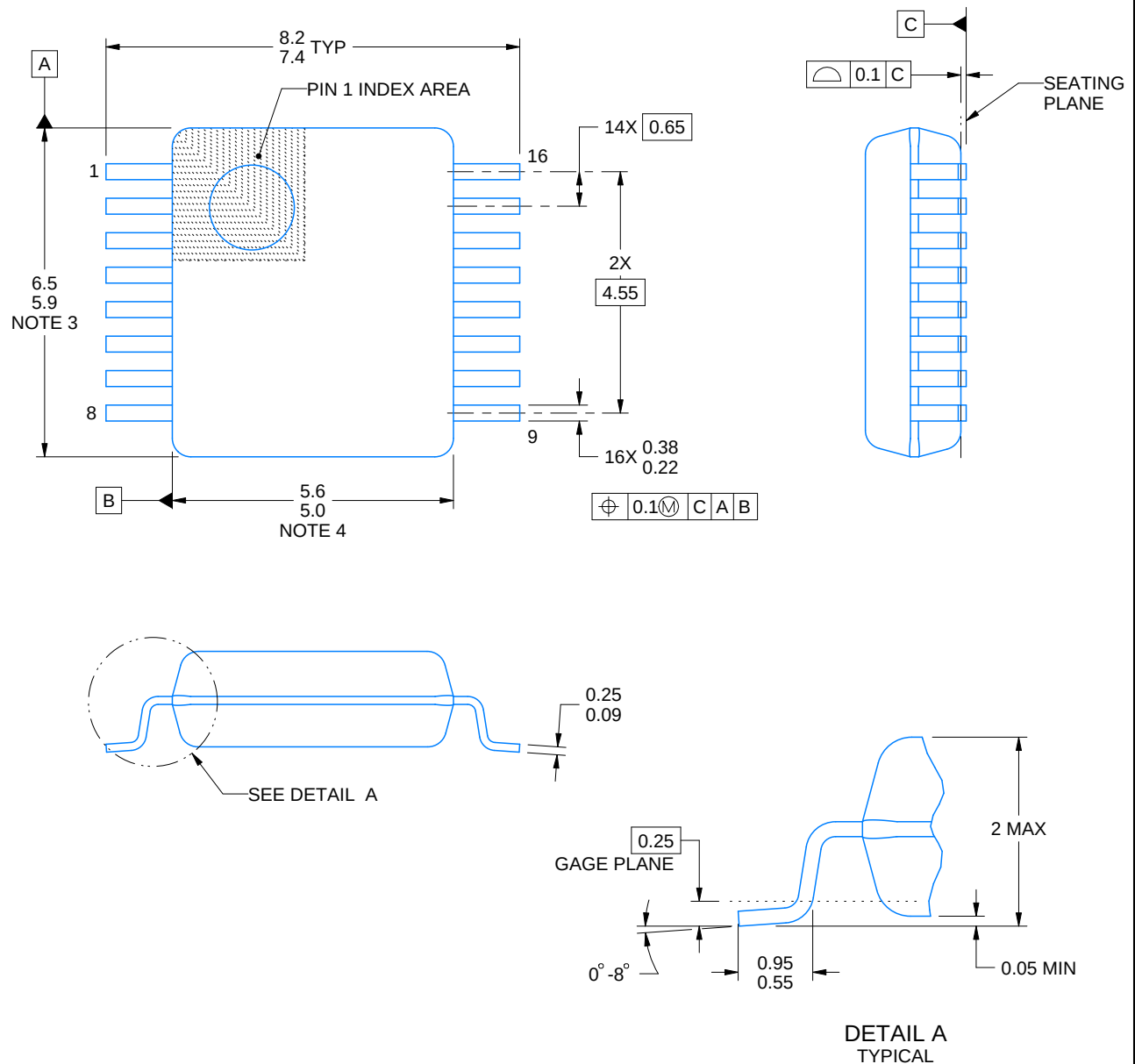


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



4220763/A 05/2022

NOTES:

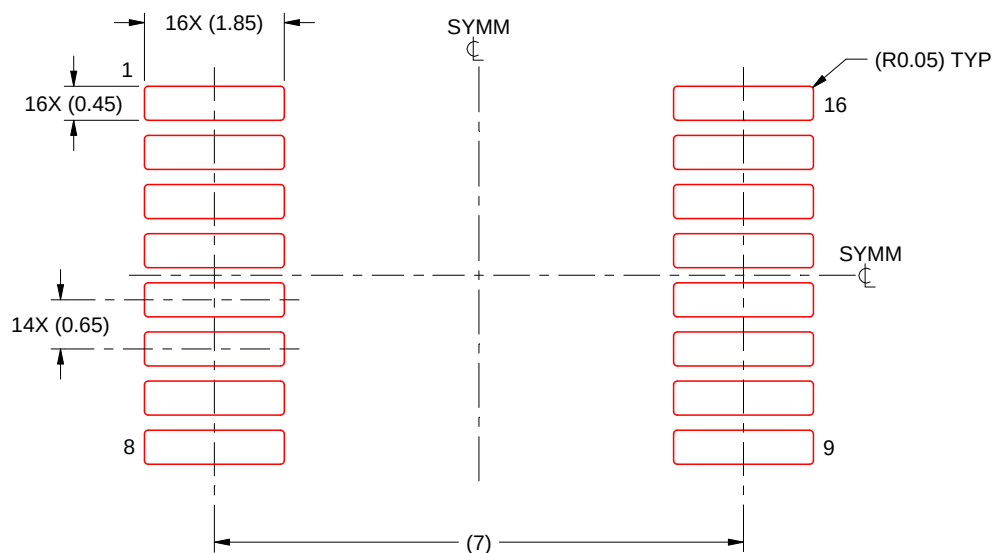
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-150.

EXAMPLE STENCIL DESIGN

DB0016A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220763/A 05/2022

NOTES: (continued)

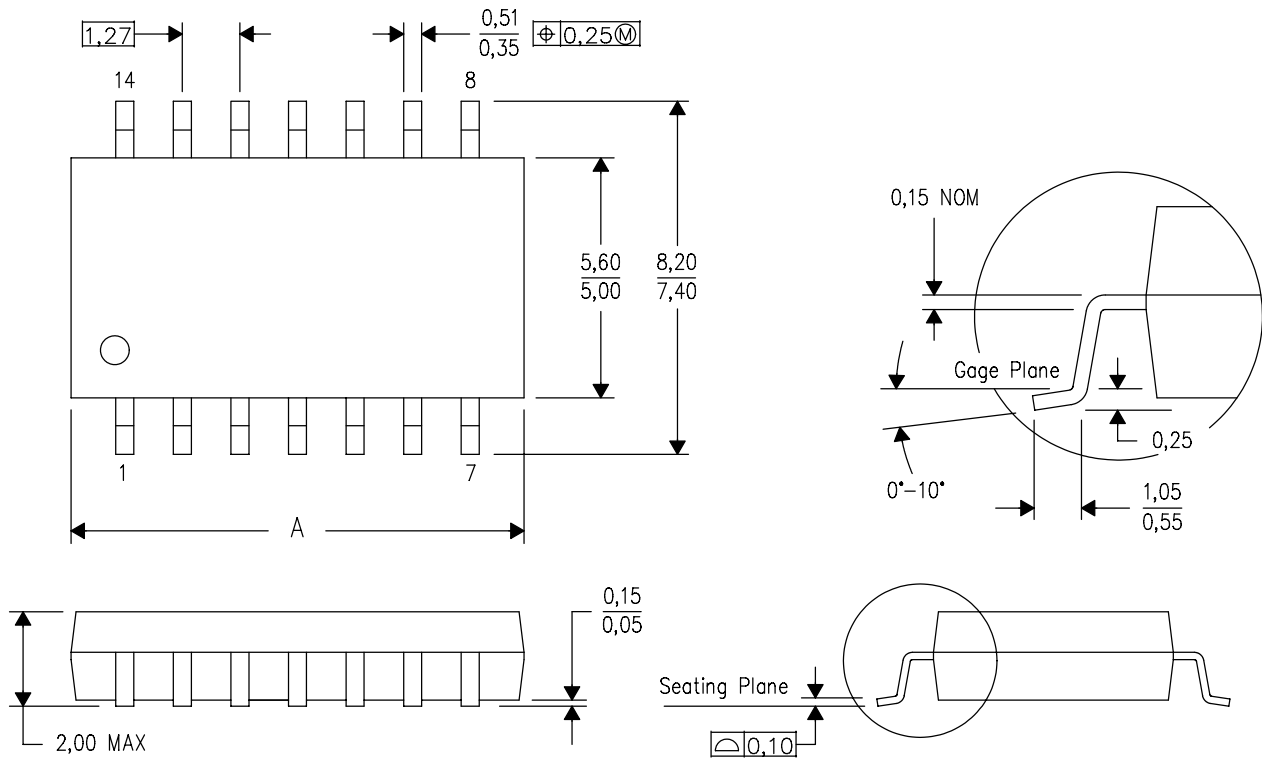
7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

MECHANICAL DATA

NS (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14-PINS SHOWN



DIM \ PINS **	14	16	20	24
A MAX	10,50	10,50	12,90	15,30
A MIN	9,90	9,90	12,30	14,70

4040062/C 03/03

- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

GENERIC PACKAGE VIEW

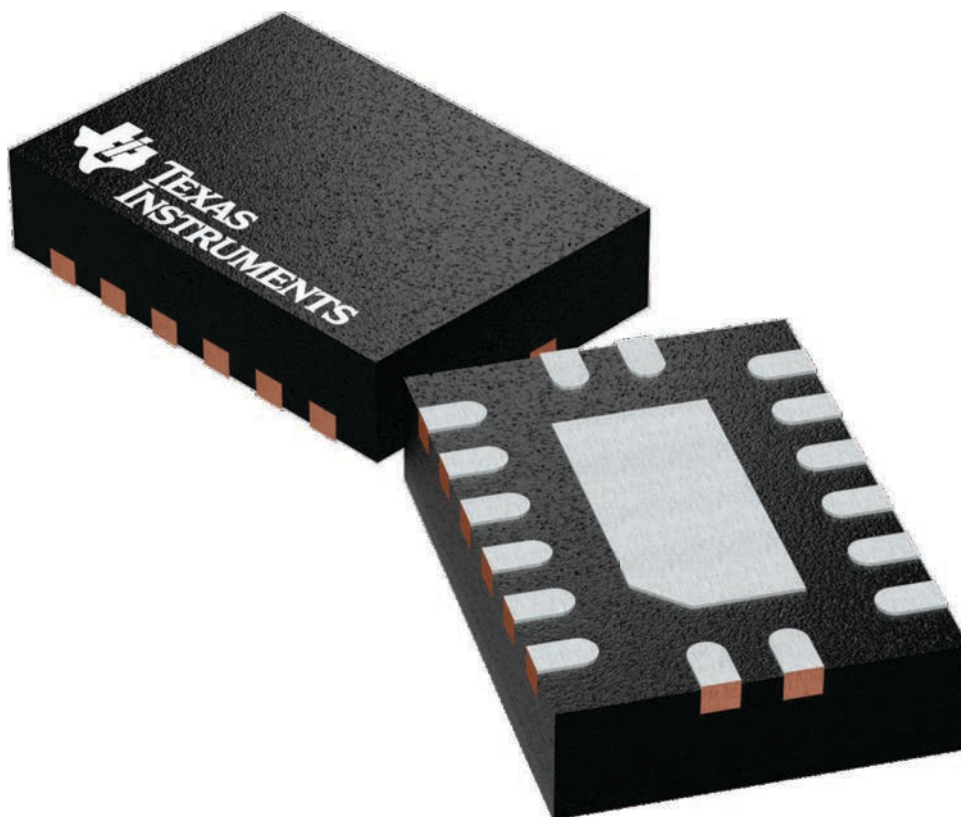
BQB 16

WQFN - 0.8 mm max height

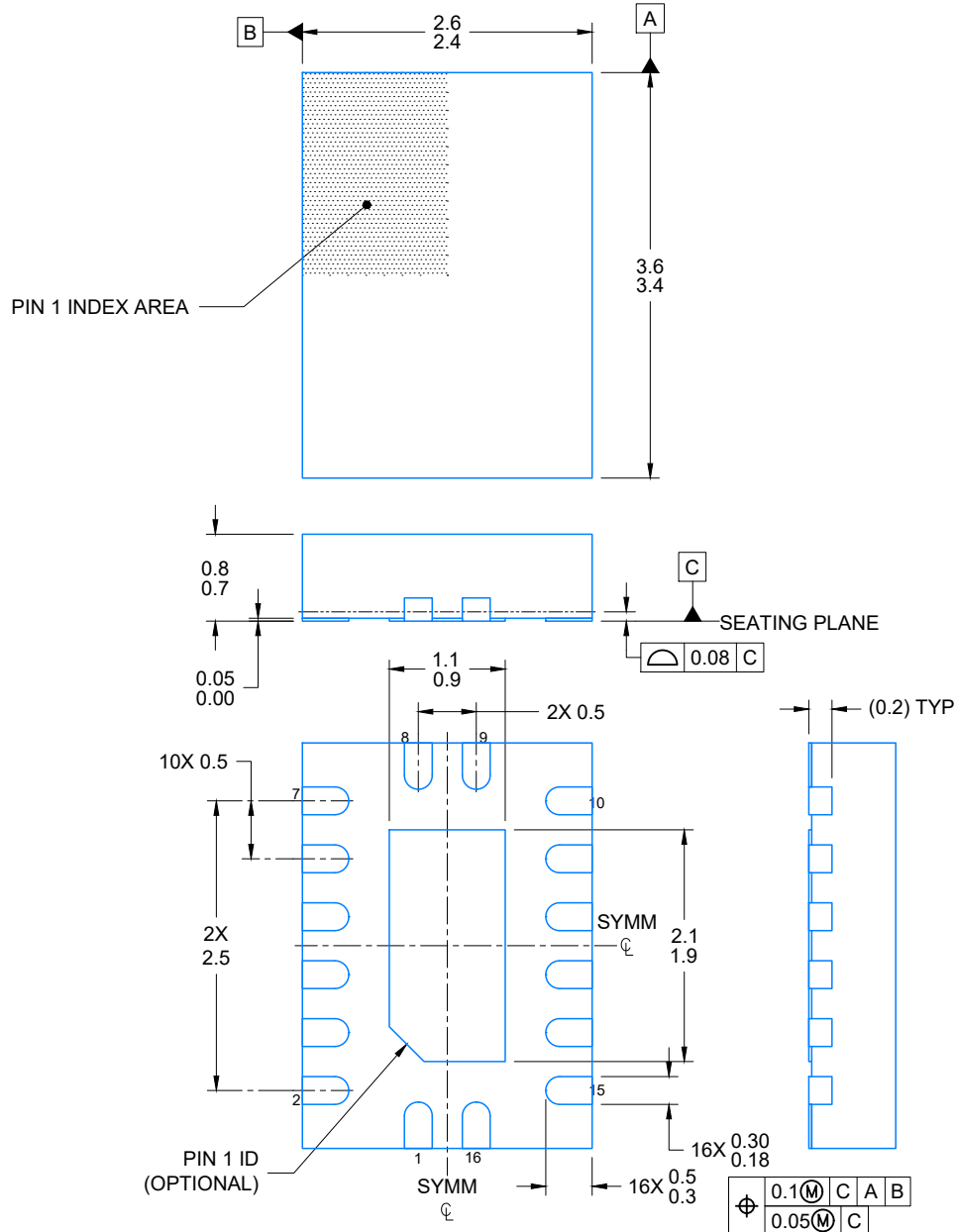
2.5 x 3.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



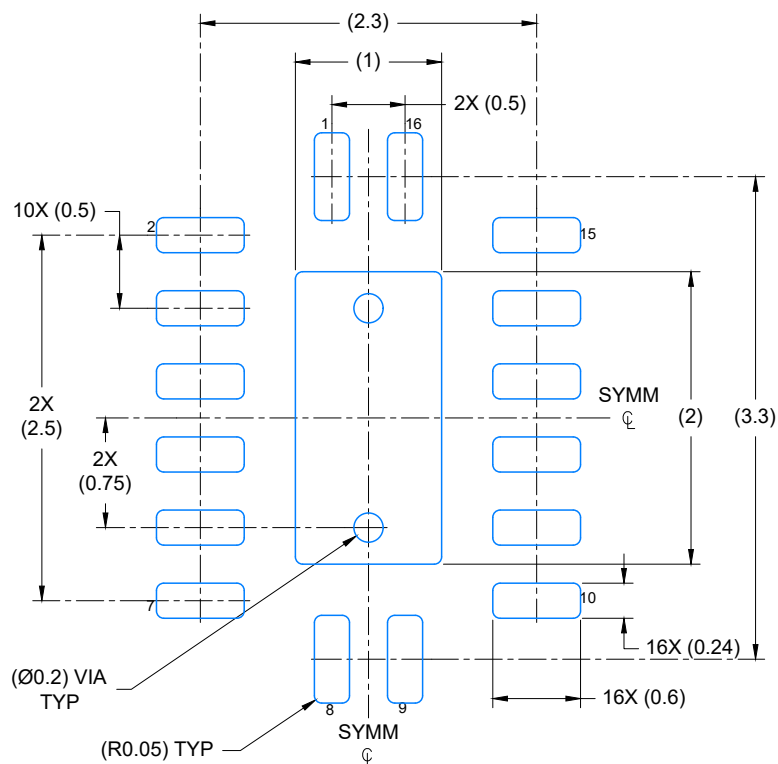
4226161/A



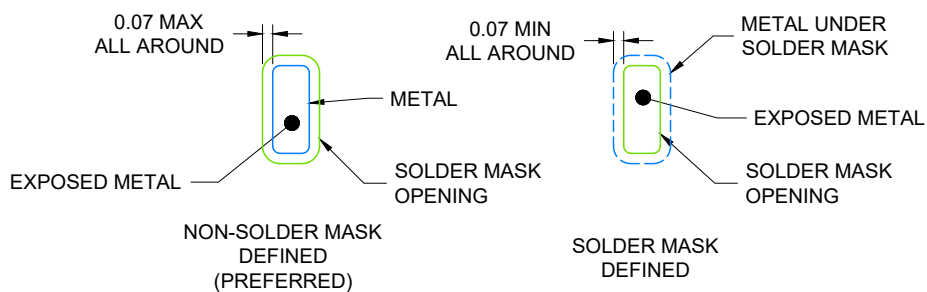
4224640/A 11/2018

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



4224640/A 11/2018

NOTES: (continued)

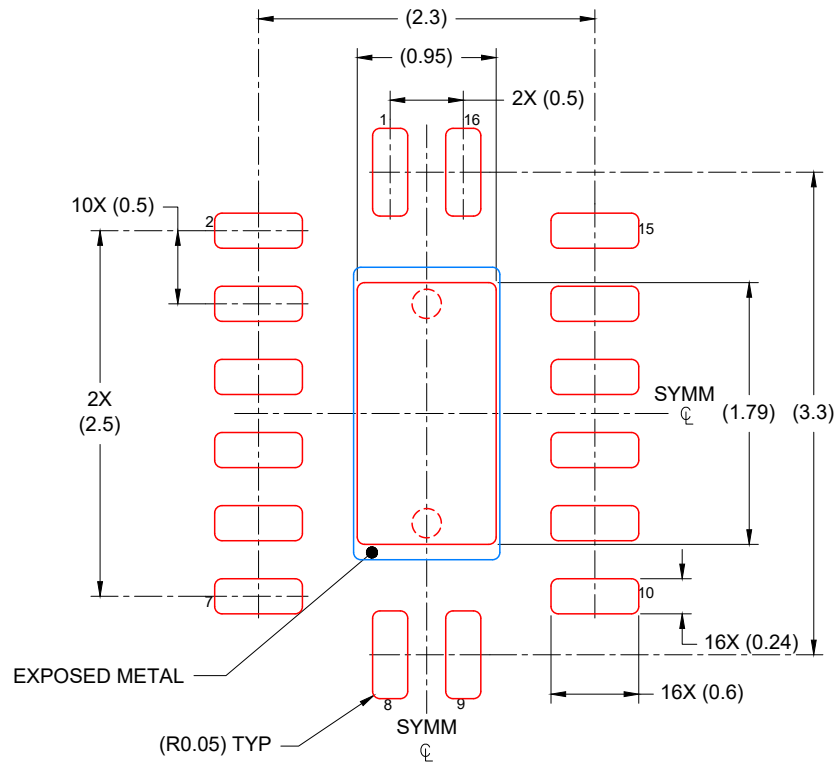
- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slue271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

BQB0016A

WQFN - 0.8 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
85% PRINTED COVERAGE BY AREA
SCALE: 20X

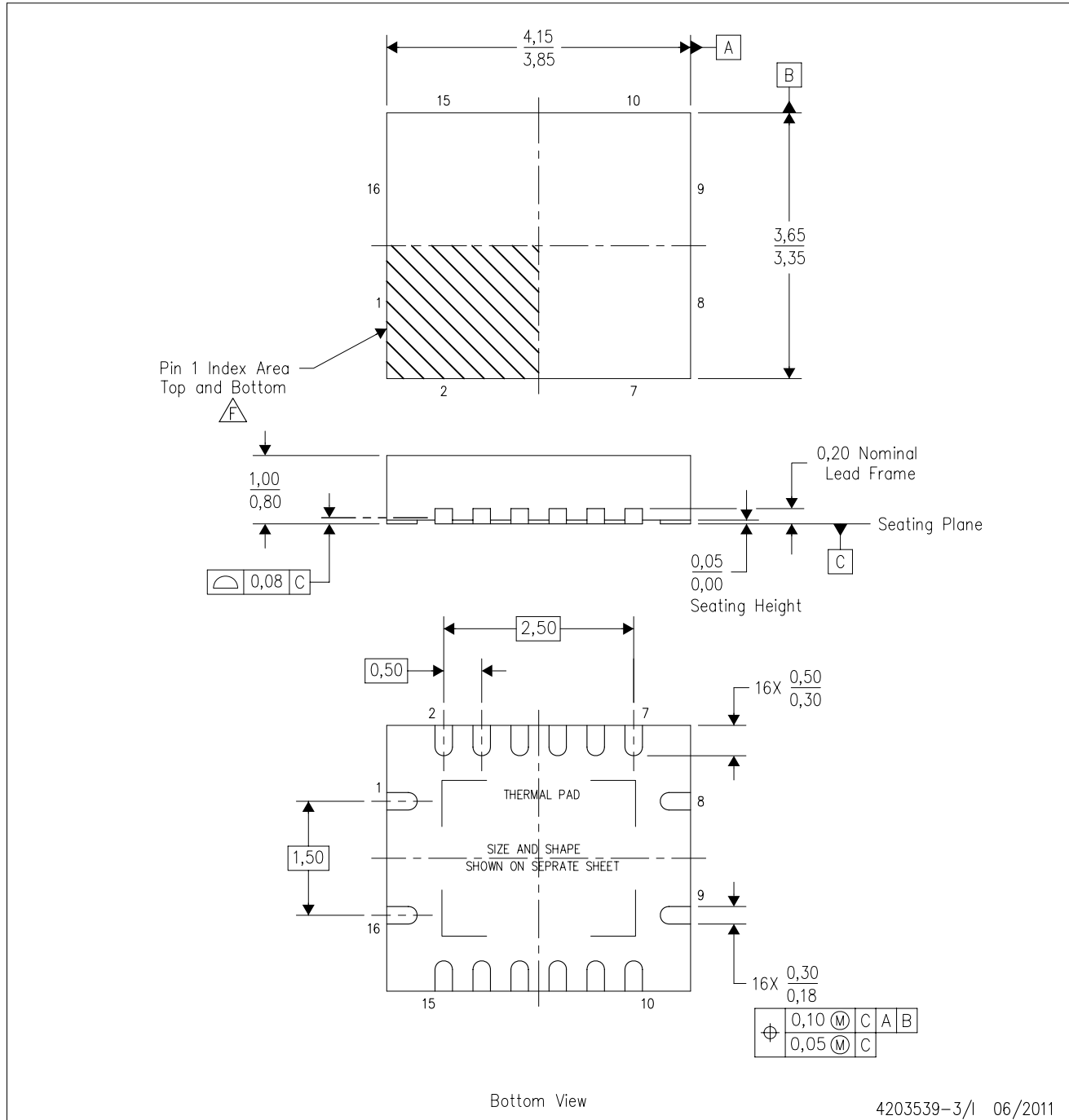
4224640/A 11/2018

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

RGY (R-PVQFN-N16)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - This drawing is subject to change without notice.
 - QFN (Quad Flatpack No-Lead) package configuration.
 - The package thermal pad must be soldered to the board for thermal and mechanical performance.
 - See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F** Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
- G. Package complies to JEDEC MO-241 variation BA.

RGY (R-PVQFN-N16)

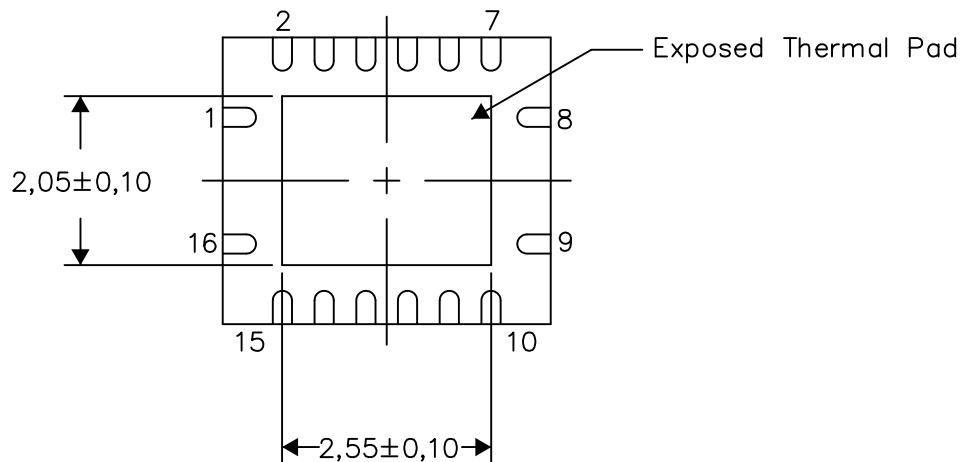
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

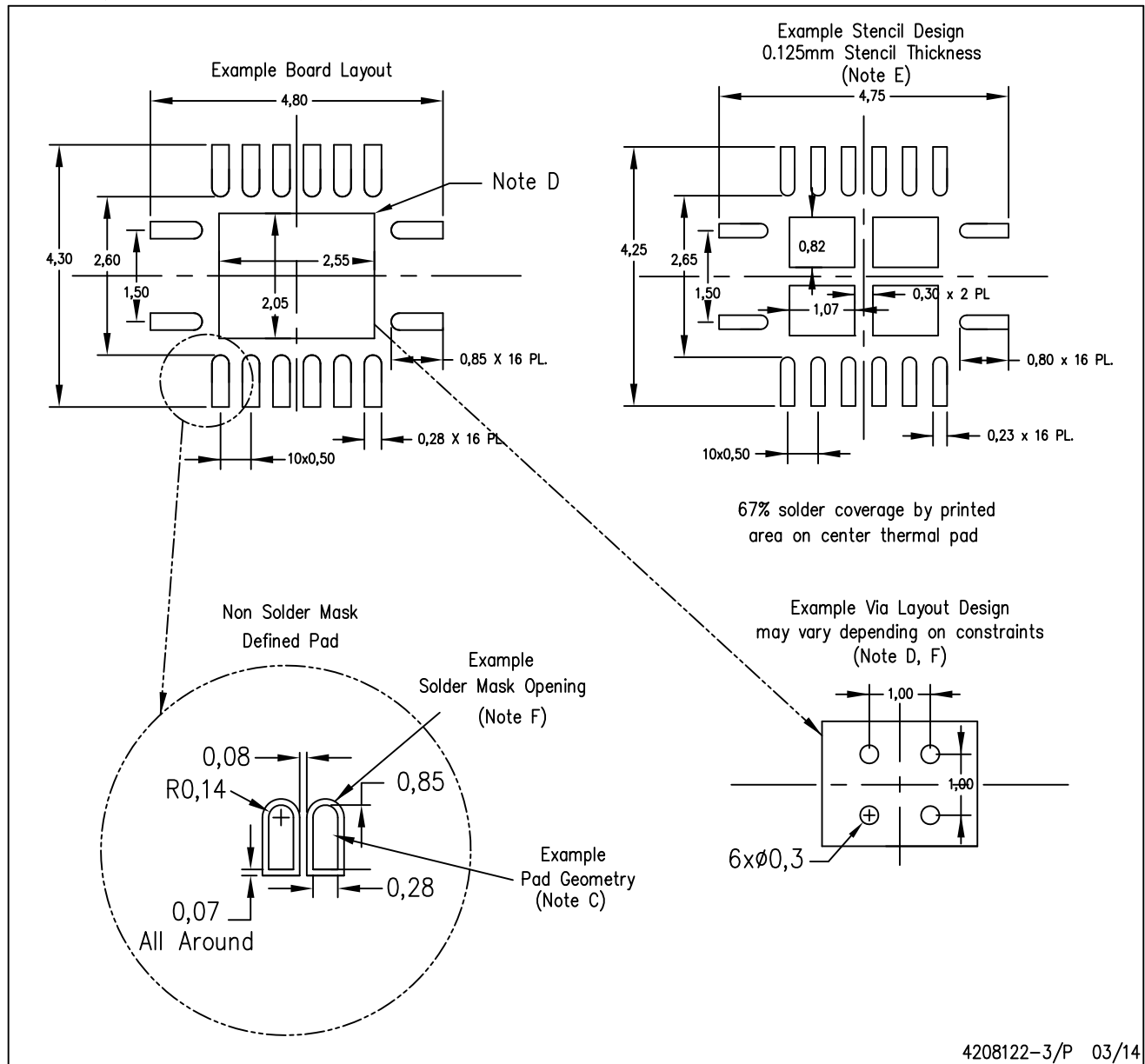
Exposed Thermal Pad Dimensions

4206353-3/P 03/14

NOTE: All linear dimensions are in millimeters

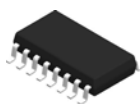
RGY (R-PVQFN-N16)

PLASTIC QUAD FLATPACK NO-LEAD



4208122-3/P 03/14

- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <<http://www.ti.com>>.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.

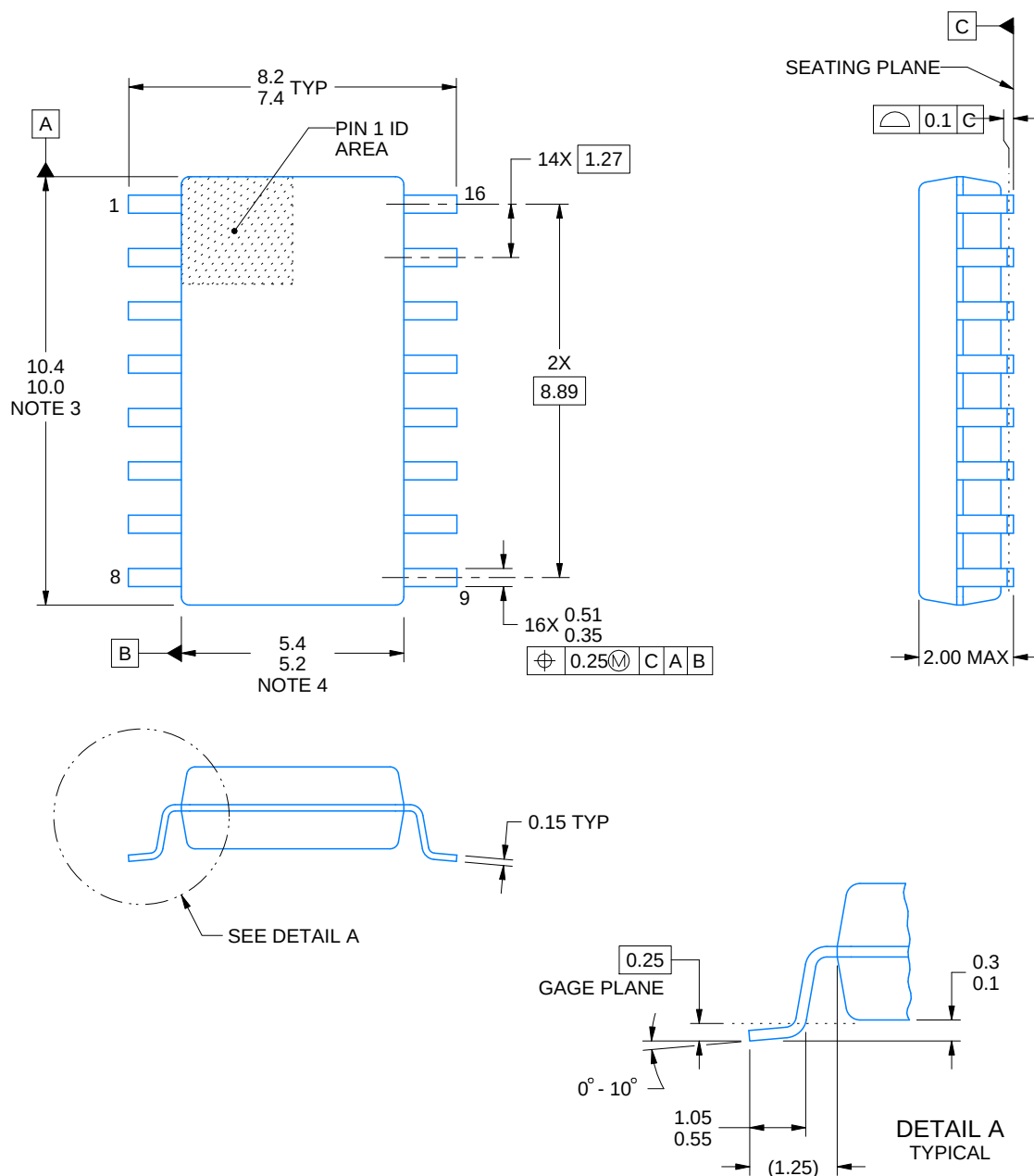


PACKAGE OUTLINE

NS0016A

SOP - 2.00 mm max height

SOP



4220735/A 12/2021

NOTES:

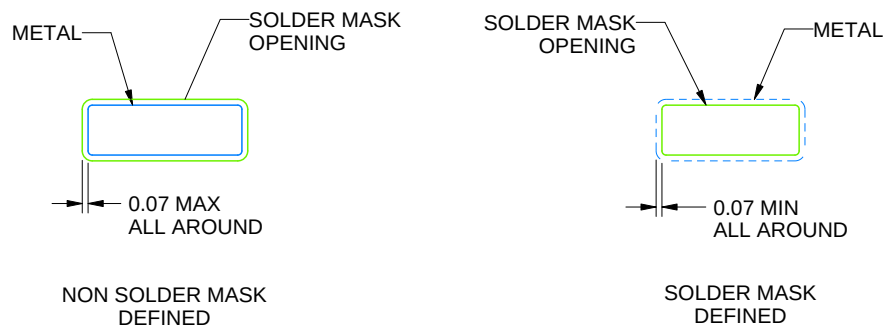
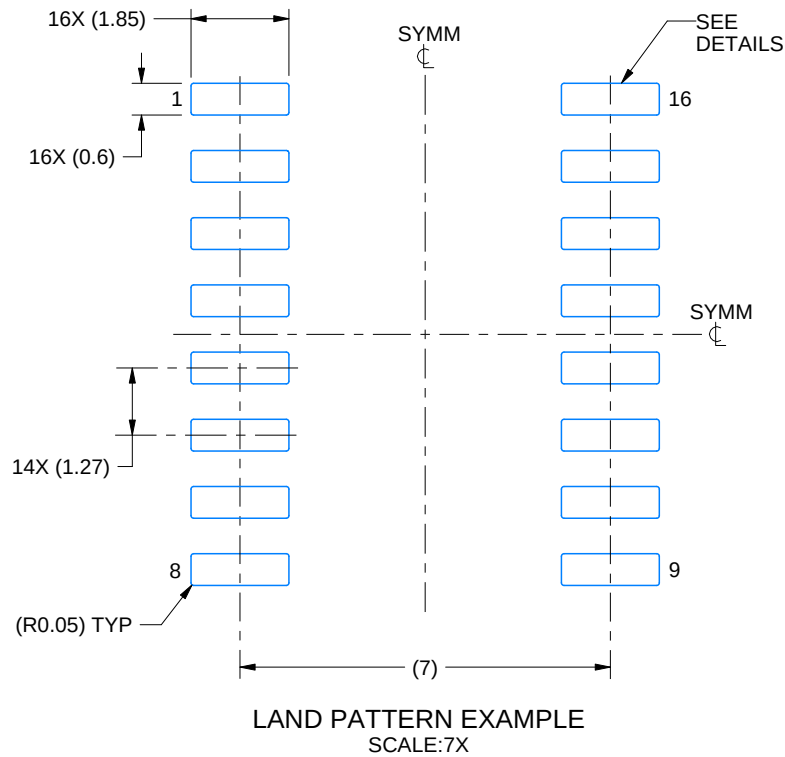
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.

EXAMPLE BOARD LAYOUT

NS0016A

SOP - 2.00 mm max height

SOP

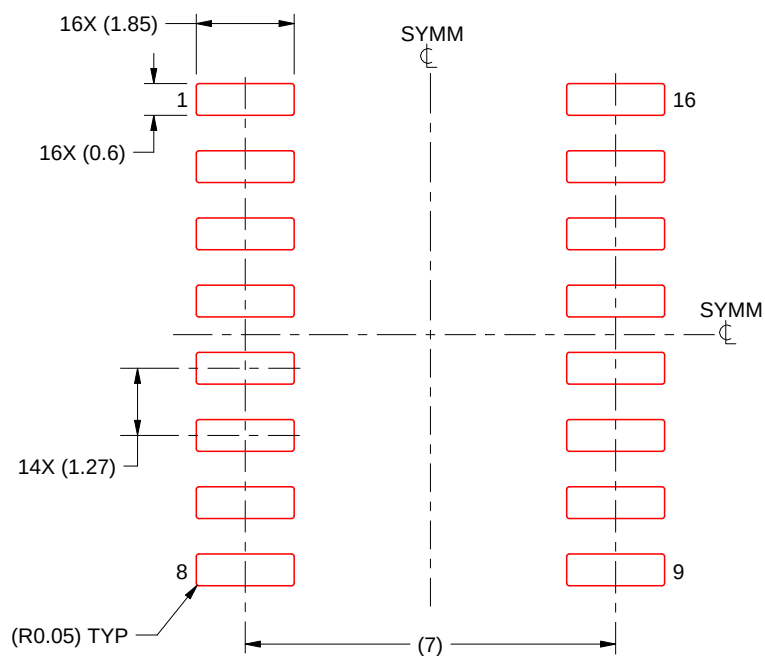


4220735/A 12/2021

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
 BASED ON 0.125 mm THICK STENCIL
 SCALE:7X

4220735/A 12/2021

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

重要声明和免责声明

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